![Texas Instruments]

3-V to 5.5-V Multichannel RS-232 Line Driver and Receiver with ±15-kV ESD Protection

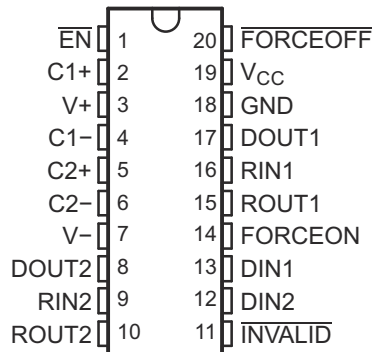## 1 Features

- ESD Protection for RS-232 bus pins
  - ±15-kV Human-body model (HBM)
  - ±8-kV IEC61000-4-2, Contact discharge
  - ±15-kV IEC61000-4-2, Air-gap discharge
- Meets or exceeds the requirements of TIA/EIA-232-F and ITU v.28 standards
- Operates with 3-V to 5.5-V V_{CC} supply
- Operates up to 500 kbit/s
- Two drivers and two receivers
- Low standby current: 1 µA typical
- External capacitors: 4 × 0.1 µF
- Accepts 5-V logic input With 3.3-V supply
- Alternative high-speed pin-compatible device (1 Mbit/s) for SNx5C3223E

2 Applications

- Battery-powered systems
- PDAs
- Notebooks
- Laptops
- Palmtop PCs
- Hand-held equipment

DB, DW, OR PW PACKAGE
(TOP VIEW)

$\overline{EN}$	1	20	$\overline{FORCEOFF}$
C1+	2	19	V_{CC}
V+	3	18	GND
C1−	4	17	DOUT1
C2+	5	16	RIN1
C2−	6	15	ROUT1
V−	7	14	FORCEON
DOUT2	8	13	DIN1
RIN2	9	12	DIN2
ROUT2	10	11	$\overline{INVALID}$

3 Description

The MAX3223E consists of two line drivers, two line receivers, and a dual charge-pump circuit with ±15-kV ESD protection pin to pin (serial-port connection pins, including GND). The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The device operates at typical data signaling rates up to 500 kbit/s and a maximum of 30-V/µs driver output slew rate.

Flexible control options for power management are available when the serial port is inactive. The auto-powerdown feature functions when FORCEON is low and $\overline{FORCEOFF}$ is high. During this mode of operation, if the device does not sense a valid RS-232 signal, the driver outputs are disabled. If $\overline{FORCEOFF}$ is set low and EN is high, both drivers and receivers are shut off, and the supply current is reduced to 1 mA. Disconnecting the serial port or turning off the peripheral drivers causes auto-powerdown to occur. Auto-powerdown can be disabled when FORCEON and $\overline{FORCEOFF}$ are high. With auto-powerdown enabled, the device is activated automatically when a valid signal is applied to any receiver input. The $\overline{INVALID}$ output is used to notify the user if an RS-232 signal is present at any receiver input. $\overline{INVALID}$ is high (valid data) if any receiver input voltage is greater than 2.7 V or less than −2.7 V, or has been between −0.3 V and 0.3 V for less than 30 µs. $\overline{INVALID}$ is low (invalid data) if the receiver input voltage is between −0.3 V and 0.3 V for more than 30 µs. Refer to Figure 5-4 for receiver input levels.

Package Information

PART NUMBER	PACKAGE[1]	PACKAGE SIZE[2]
MAX3223E	SOIC (DW, 20)	12.8 mm × 10.3 mm
	SSOP (DB, 20)	7.2 mm × 7.8 mm
	TSSOP (PW, 20)	6.5 mm x 6.4 mm

(1) For more information, see Section 10.
(2) The package size (length × width) is a nominal value and includes pins, where applicable.

Table of Contents

Product Folder Links: *MAX3223E*

4 Specifications

4.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) [1]

				MIN	MAX	UNIT
V_{CC}	Supply voltage range			−0.3	6	V
V+	Positive-output supply voltage range[2]			−0.3	7	V
V−	Negative-output supply voltage range[2]			0.3	−7	V
V+ − V−	Supply voltage difference[2]				13	V
V_I	Input voltage range	Driver ($\overline{\text{FORCEOFF}}$, FORCEON, $\overline{\text{EN}}$)		−0.3	6	V
		Receiver		−25	25	
V_O	Output voltage range	Driver		−13.2	13.2	V
		Receiver ($\overline{\text{INVALID}}$)		−0.3	V_{CC} + 0.3	
T_J	Operating virtual junction temperature				150	°C
T_{stg}	Storage temperature range			−65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to network GND.

4.2 Recommended Operating Conditions

See Figure 7-1, and [1]

				MIN	NOM	MAX	UNIT
	Supply voltage		V_{CC} = 3.3 V	3	3.3	3.6	V
			V_{CC} = 5 V	4.5	5	5.5	
V_{IH}	Driver and control high-level input voltage	DIN, $\overline{\text{EN}}$, $\overline{\text{FORCEOFF}}$, FORCEON	V_{CC} = 3.3 V	2			V
			V_{CC} = 5 V	2.4			
V_{IL}	Driver and control low-level input voltage	DIN, $\overline{\text{EN}}$, $\overline{\text{FORCEOFF}}$, FORCEON				0.8	V
V_I	Driver and control input voltage	DIN, $\overline{\text{EN}}$, $\overline{\text{FORCEOFF}}$, FORCEON		0		5.5	V
	Receiver input voltage			−25		25	V
T_A	Operating free-air temperature	MAX3223EC		0		70	°C
		MAX3223EI		−40		85	

(1) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

4.3 ESD Ratings

				VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001[1]	All pins except RIN1, RIN2, DOUT1 and DOUT2 pins	±3000	V
			RIN1, RIN2, DOUT1 and DOUT2 pins to GND	±15000	
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002[2]	All pins	±1500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

4.4 ESD Ratings - IEC Specifications

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	IEC 61000-4-2 Contact Discharge[1]	±8000	V
		IEC 61000-4-2 Air-gap Discharge[1]	±15,000	

(1)   A minimum of 1-µF capacitor between V_{CC} and GND is required to meet the specified IEC 61000-4-2 rating.

4.5 Thermal Information

	THERMAL METRIC[1]	DB (SOIC)	DW (SOIC)	PW (TSSOP)	UNIT
		20 PINS	20 PINS	20 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	87.2	76.8	89.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	41.1	39.6	29.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	43.3	41.5	41.9	°C/W
ψ_{JT}	Junction-to-top characterization parameter	9.2	12.6	1.9	°C/W
ψ_{JB}	Junction-to-board characterization parameter	42.7	40.9	41.3	°C/W

(1)   For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

4.6 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5-5) and [1]

	PARAMETER		TEST CONDITIONS	MIN	TYP[2]	MAX	UNIT
I_I	Input leakage current	EN, FORCEOFF, FORCEON			±0.01	±1	µA
I_{CC}	Supply current	Auto-powerdown disabled	V_{CC} = 3.3 V or 5 V, T_A = 25°C, No load, FORCEOFF and FORCEON at V_{CC}		0.3	1.3	mA
		Powered off	No load, FORCEOFF at GND		1	10	µA
		Auto-powerdown enabled	No load, FORCEOFF at V_{CC}, FORCEON at GND, All RIN are open or grounded		1	10	

(1)   Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2)   All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

4.7 Driver Section

4.7.1 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5-5) and [1]

	PARAMETER	TEST CONDITIONS	MIN	TYP[2]	MAX	UNIT
V_{OH}	High-level output voltage	DOUT at R_L = 3 kΩ to GND	5	5.4		V
V_{OL}	Low-level output voltage	DOUT at R_L = 3 kΩ to GND	–5	–5.4		V
I_{IH}	High-level input current	V_I = V_{CC}		±0.01	±1	µA
I_{IL}	Low-level input current	V_I at GND		±0.01	±1	µA
I_{OS}	Short-circuit output current[3]	V_{CC} = 3.6 V, V_O = 0 V		±35	±60	mA
		V_{CC} = 5.5 V, V_O = 0 V				
r_o	Output resistance	V_{CC}, V+, and V– = 0 V, V_O = ±2 V	300	10M		Ω
I_{OZ}	Output leakage current	FORCEOFF = GND, V_{CC} = 3 V to 3.6 V, V_O = ±12 V			±25	µA
		FORCEOFF = GND, V_{CC} = 4.5 V to 5.5 V, V_O = ±12 V			±25	

(1)   Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2)   All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(3)   Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

4.7.2 Switching Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5-5) and [1]

PARAMETER		TEST CONDITIONS		MIN	TYP[2]	MAX	UNIT
	Maximum data rate	C_L = 1000 pF, One DOUT switching,	R_L = 3 kΩ, See Figure 5-1	250	500		kbit/s
$t_{sk(p)}$	Pulse skew[3]	C_L = 150 pF to 2500 pF, See Figure 5-2	R_L = 3 kΩ to 7 kΩ,		100		ns
SR(tr)	Slew rate, transition region (See Figure 5-1)	R_L = 3 kΩ to 7 kΩ, V_{CC} = 3.3 V	C_L = 150 pF to 1000 pF	6		30	V/µs
			C_L = 150 pF to 2500 pF	4		30	

(1)   Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2)   All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(3)   Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.

4.7.3 ESD Protection

		TYP	UNIT
Driver outputs (DOUTx)	Human-Body Model (HBM)	±15	kV
	IEC61000-4-2, Air-Gap Discharge	±15	
	IEC61000-4-2, Contact Discharge	±8	

4.8 Receiver Section

4.8.1 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 7-1) and [1]

PARAMETER		TEST CONDITIONS	MIN	TYP[2]	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = −1 mA	V_{CC} − 0.6	V_{CC} − 0.1		V
V_{OL}	Low-level output voltage	I_{OL} = 1.6 mA			0.4	V
V_{IT+}	Positive-going input threshold voltage	V_{CC} = 3.3 V		1.6	2.4	V
		V_{CC} = 5 V		1.9	2.4	
V_{IT-}	Negative-going input threshold voltage	V_{CC} = 3.3 V	0.6	1.1		V
		V_{CC} = 5 V	0.6	1.4		
V_{hys}	Input hysteresis (V_{IT+} − V_{IT-})			0.5		V
I_{OZ}	Output leakage current	$\overline{EN}$ = V_{CC}		±0.05		µA
r_i	Input resistance	V_I = ±3 V to ±25 V	3	5		kΩ

(1)   Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2)   All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

4.8.2 Switching Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) [1]

PARAMETER		TEST CONDITIONS	TYP[2]	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	C_L = 150 pF, See Figure 5-3	150	ns
t_{PHL}	Propagation delay time, high- to low-level output	C_L = 150 pF, See Figure 5-3	150	ns
t_{en}	Output enable time	C_L = 150 pF, R_L = 3 kΩ, See Figure 5-4	200	ns
t_{dis}	Output disable time	C_L = 150 pF, R_L = 3 kΩ, See Figure 5-4	200	ns
$t_{sk(p)}$	Pulse skew[3]	See Figure 5-3	50	ns

(1)   Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

(2)   All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(3)   Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.

4.8.3 ESD Protection

		TYP	UNIT
Receiver inputs (RINx)	Human-Body Model (HBM)	±15	kV
	IEC61000-4-2, Air-Gap Discharge	±15	
	IEC61000-4-2, Contact Discharge	±8	

4.9 Auto-Powerdown Section

4.9.1 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5-5)

| PARAMETER		TEST CONDITIONS		MIN	MAX	UNIT
$V_{T+(valid)}$	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND,	FORCEOFF = V_{CC}		2.7	V
$V_{T(valid)}$	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND,	FORCEOFF = V_{CC}	−2.7		V
$V_{T(invalid)}$	Receiver input threshold for INVALID low-level output voltage	FORCEON = GND,	FORCEOFF = V_{CC}	−0.3	0.3	V
V_{OH}	INVALID high-level output voltage	I_{OH} = 1 mA, FORCEOFF = V_{CC}	FORCEON = GND,	V_{CC} − 0.6		V
V_{OL}	INVALID low-level output voltage	I_{OL} = 1.6 mA, FORCEOFF = V_{CC}	FORCEON = GND,		0.4	V

4.9.2 Switching Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5-5)

| PARAMETER		TYP[1]	UNIT
t_{valid}	Propagation delay time, low- to high-level output	1	µs
$t_{invalid}$	Propagation delay time, high- to low-level output	30	µs
t_{en}	Supply enable time	100	µs

(1)   All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

5 Parameter Measurement Information
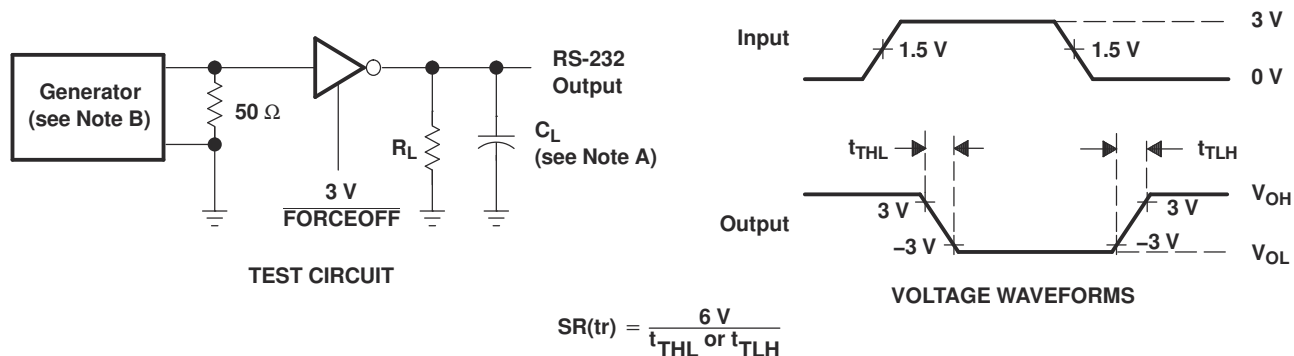
TEST CIRCUIT

VOLTAGE WAVEFORMS

$$SR(tr) = \frac{6\ V}{t_{THL}\ \text{or}\ t_{TLH}}$$
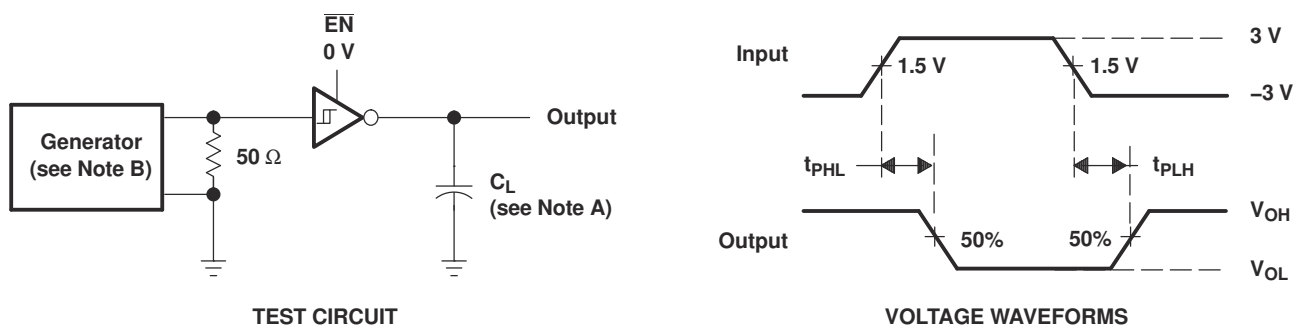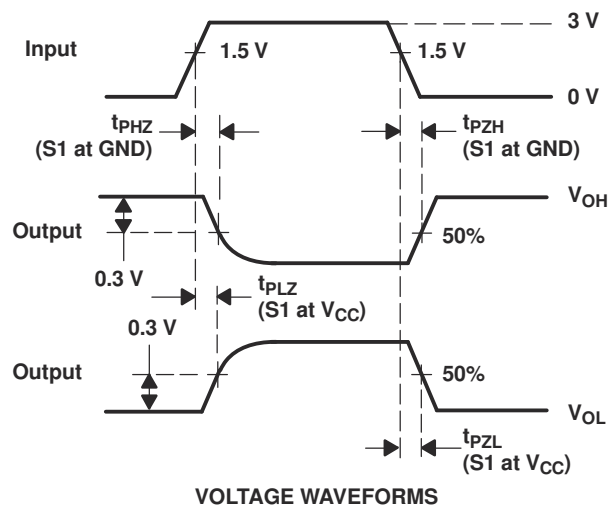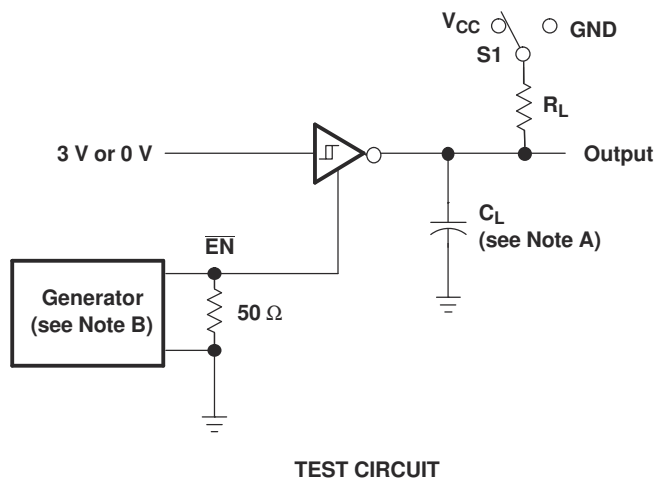
A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.

Figure 5-1. Driver Slew Rate
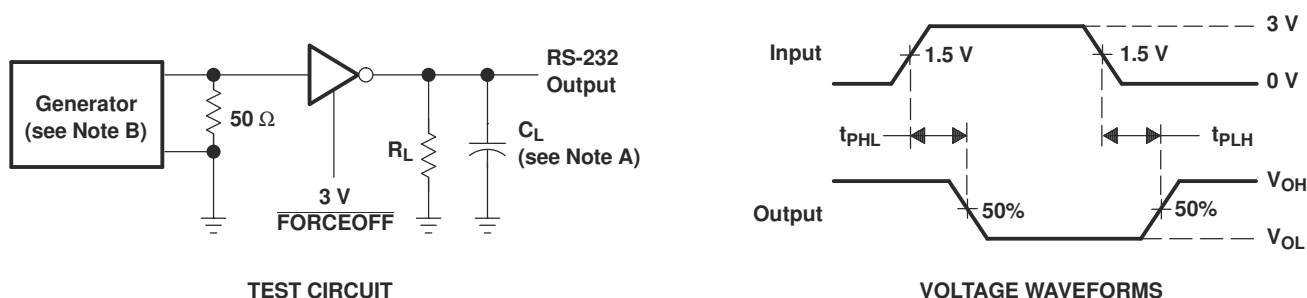
TEST CIRCUIT

VOLTAGE WAVEFORMS

A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.

Figure 5-2. Driver Pulse Skew

TEST CIRCUIT

VOLTAGE WAVEFORMS
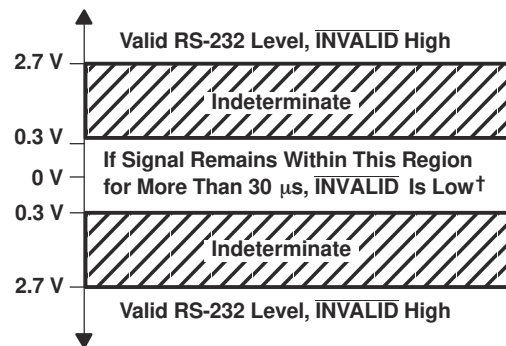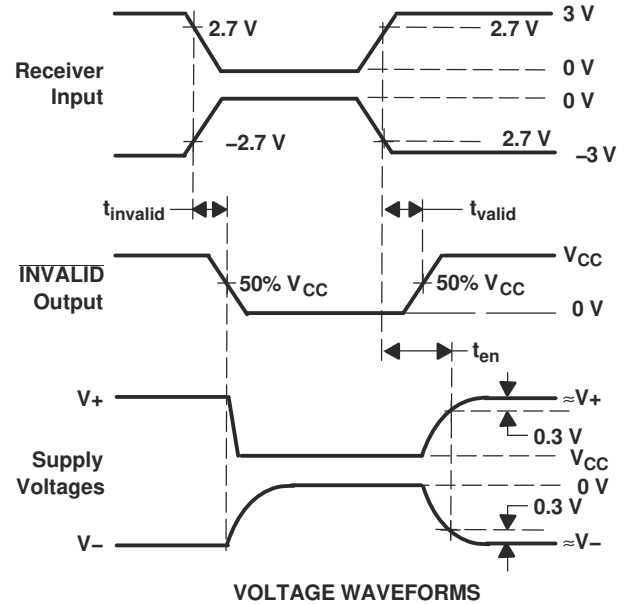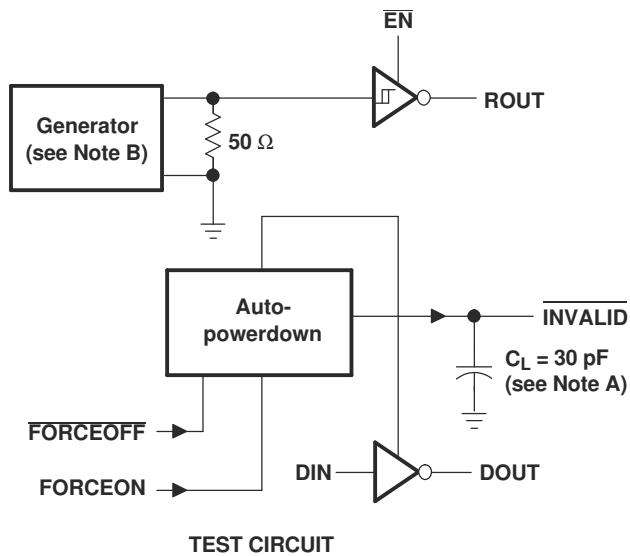
A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.

Figure 5-3. Receiver Propagation Delay Times

Product Folder Links: *MAX3223E*

TEST CIRCUIT

VOLTAGE WAVEFORMS

A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.

Figure 5-4. Receiver Enable and Disable Times

Product Folder Links: *MAX3223E*

TEST CIRCUIT

VOLTAGE WAVEFORMS

† Auto-powerdown disables drivers and reduces supply current to 1 μA

A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.

Figure 5-5. INVALID Propagation Delay Times and Supply Enabling Time

6 Detailed Description

6.1 Functional Block Diagram
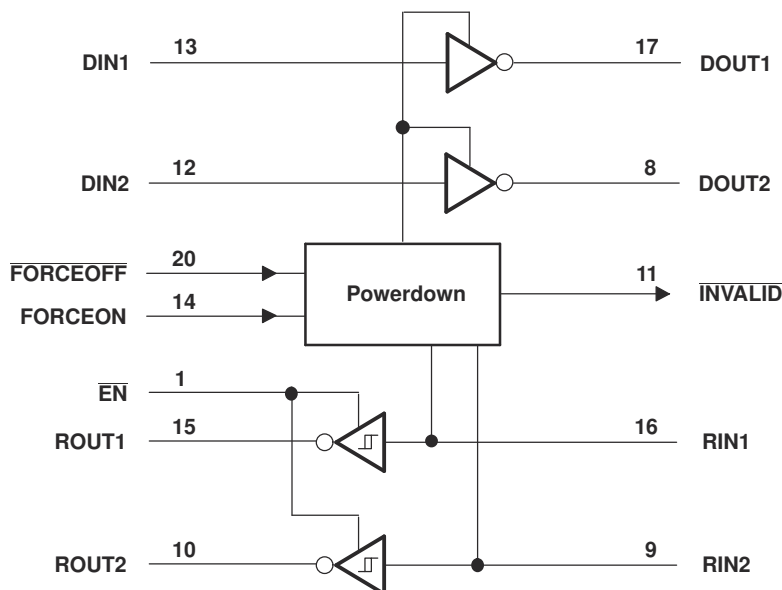
Pin numbers are for the DB, DW, and PW packages.

Figure 6-1. Logic diagram (positive logic)

6.2 Device Functional Modes

Function Table (Each Driver)

INPUTS[1]				OUTPUT DOUT	DRIVER STATUS
DIN	FORCEON	FORCEOFF	VALID RIN RS-232 LEVEL		
X	X	L	X	Z	Powered off
L	H	H	X	H	Normal operation with auto-powerdown disabled
H	H	H	X	L	Normal operation with auto-powerdown disabled
L	L	H	Yes	H	Normal operation with auto-powerdown enabled
H	L	H	Yes	L	Normal operation with auto-powerdown enabled
L	L	H	No	Z	Powered off by auto-powerdown feature
H	L	H	No	Z	Powered off by auto-powerdown feature

(1)   H = high level, L = low level, X = irrelevant, Z = high impedance

Function Table (Each Receiver)

| INPUTS[1]			OUTPUT DOUT
RIN	EN	VALID RIN RS-232 LEVEL	
L	L	X	H
H	L	X	L
X	H	X	Z
Open	L	No	H

(1)   H = high level, L = low level, X = irrelevant,
Z = high impedance (off),
Open = input disconnected or connected driver off

Product Folder Links: *MAX3223E*

7 Application and Implementation

> **Note**
>
> Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

7.1 Typical Application
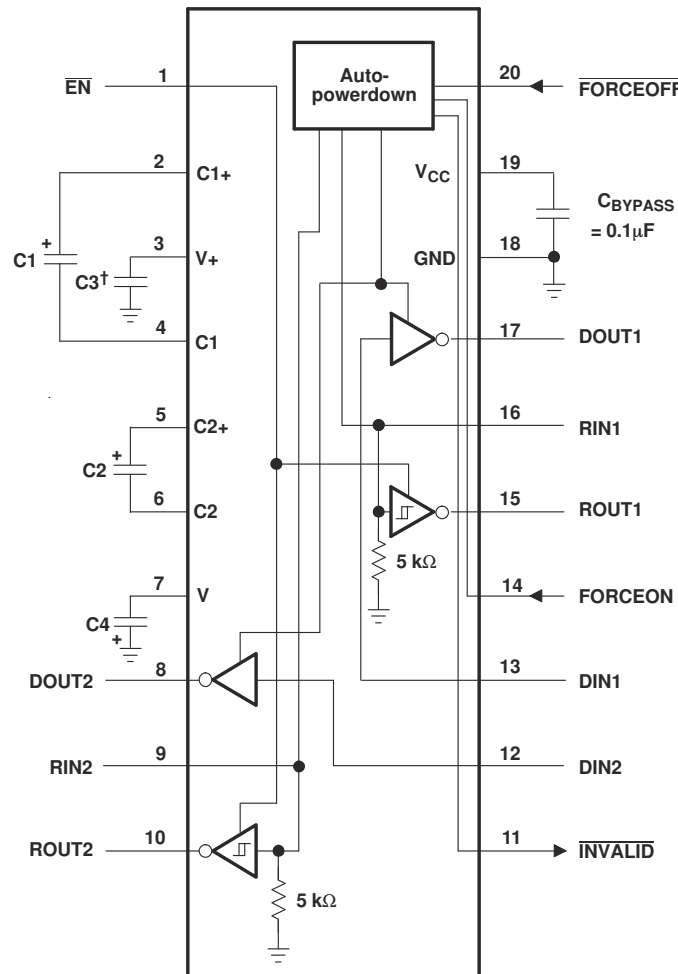
† C3 can be connected to V_{CC} or GND.

NOTES: A. Resistor values shown are nominal.

B. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

V_{CC} vs CAPACITOR VALUES

V_{CC}	C1	C2, C3, and C4
3.3 V ± 0.3 V	0.1 µF	0.1 µF
5 V ± 0.5 V	0.047 µF	0.33 µF
3 V to 5.5 V	0.1 µF	0.47 µF

Figure 7-1. Typical Operating Circuit and Capacitor Values

7.1.1 Detailed Design Procedure

MAX3223E has integrated charge-pump that generates positive and negative rails needed for RS-232 signal levels. Main design requirement is that charge-pump capacitor terminals must be connected with recommended capacitor values. Charge-pump rail voltages and device supply pin must be properly bypassed with ceramic capacitors

(1)

8 Device and Documentation Support

8.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.2 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

8.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.
All trademarks are the property of their respective owners.

8.4 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.5 Glossary

TI Glossary   This glossary lists and explains terms, acronyms, and definitions.

9 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGE OPTION ADDENDUM

PACKAGING INFORMATION

Orderable part number (1)	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
MAX3223ECDBR	Obsolete	Production	SSOP (DB) | 20	-	-	Call TI	Call TI	0 to 70	MP223EC
MAX3223ECDW	Active	Production	SOIC (DW) | 20	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3223EC
MAX3223ECDW.A	Active	Production	SOIC (DW) | 20	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3223EC
MAX3223ECDWR	Active	Production	SOIC (DW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3223EC
MAX3223ECDWR.A	Active	Production	SOIC (DW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3223EC
MAX3223ECPW	Obsolete	Production	TSSOP (PW) | 20	-	-	Call TI	Call TI	0 to 70	MP223EC
MAX3223ECPWR	Obsolete	Production	TSSOP (PW) | 20	-	-	Call TI	Call TI	0 to 70	MP223EC
MAX3223EIDB	Obsolete	Production	SSOP (DB) | 20	-	-	Call TI	Call TI	-40 to 85	MP223EI
MAX3223EIDBR	Active	Production	SSOP (DB) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP223EI
MAX3223EIDBR.A	Active	Production	SSOP (DB) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP223EI
MAX3223EIDBRG4	Active	Production	SSOP (DB) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP223EI
MAX3223EIDBRG4.A	Active	Production	SSOP (DB) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP223EI
MAX3223EIDW	Active	Production	SOIC (DW) | 20	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3223EI
MAX3223EIDW.A	Active	Production	SOIC (DW) | 20	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3223EI
MAX3223EIDWR	Active	Production	SOIC (DW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3223EI
MAX3223EIDWR.A	Active	Production	SOIC (DW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3223EI
MAX3223EIPWR	Active	Production	TSSOP (PW) | 20	2000 | LARGE T&R	Yes	NIPDAU | NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP223EI
MAX3223EIPWR.A	Active	Production	TSSOP (PW) | 20	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP223EI

(1) Status: For more details on status, see our product life cycle.

(2) Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

![Texas Instruments logo]

PACKAGE MATERIALS INFORMATION

TAPE AND REEL INFORMATION

REEL DIMENSIONS

TAPE DIMENSIONS

A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
MAX3223ECDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
MAX3223EIDBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
MAX3223EIDBRG4	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
MAX3223EIDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
MAX3223EIPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
MAX3223ECDWR	SOIC	DW	20	2000	356.0	356.0	45.0
MAX3223EIDBR	SSOP	DB	20	2000	353.0	353.0	32.0
MAX3223EIDBRG4	SSOP	DB	20	2000	353.0	353.0	32.0
MAX3223EIDWR	SOIC	DW	20	2000	356.0	356.0	45.0
MAX3223EIPWR	TSSOP	PW	20	2000	353.0	353.0	32.0

TUBE

T - Tube height

L - Tube length

W - Tube width

B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
MAX3223ECDW	DW	SOIC	20	25	507	12.83	5080	6.6
MAX3223ECDW.A	DW	SOIC	20	25	507	12.83	5080	6.6
MAX3223EIDW	DW	SOIC	20	25	507	12.83	5080	6.6
MAX3223EIDW.A	DW	SOIC	20	25	507	12.83	5080	6.6

4214851/B   08/2019

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-150.

20X (1.85)

1

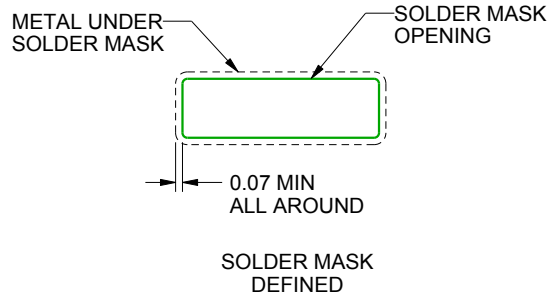20X (0.45)

18X (0.65)

SYMM

(R0.05) TYP

20

SYMM

10

11

(7)

LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

SOLDER MASK
OPENING

METAL

EXPOSED METAL

0.07 MAX
ALL AROUND

NON-SOLDER MASK
DEFINED
(PREFERRED)

METAL UNDER
SOLDER MASK

SOLDER MASK
OPENING

EXPOSED METAL

0.07 MIN
ALL AROUND
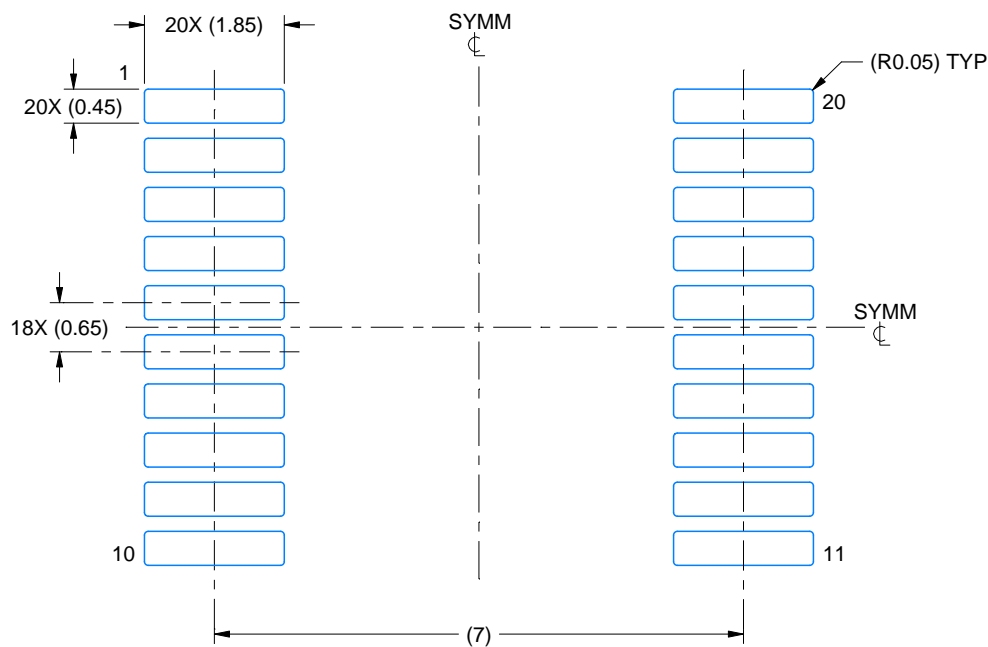
SOLDER MASK
DEFINED
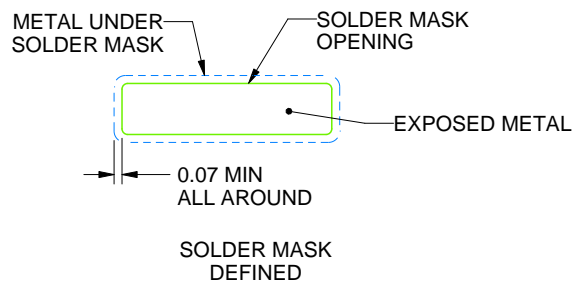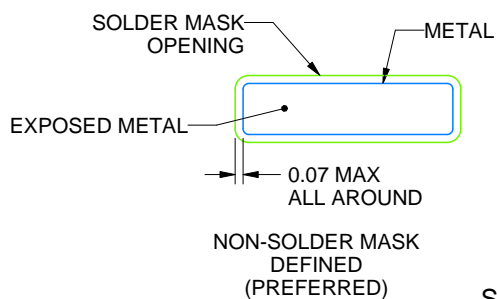
SOLDER MASK DETAILS

4214851/B   08/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4214851/B   08/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

10.63
9.97 TYP

A

PIN 1 ID
AREA

1

18X 1.27

20

13.0
12.6
NOTE 3

2X
11.43

10

11

B

7.6
7.4
NOTE 4

20X 0.51
0.31

⊕ 0.25 Ⓜ C A B

C

SEATING PLANE

⌒ 0.1 C

2.65 MAX

0.33 TYP
0.10

SEE DETAIL A

0.25
GAGE PLANE

0° - 8°

1.27
0.40

0.3
0.1

DETAIL A
TYPICAL

4220724/A 05/2016

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing
   per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
   exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.

20X (2)

SYMM

1

20

20X (0.6)

18X (1.27)

SYMM

(R0.05)
TYP

10

11

(9.3)

LAND PATTERN EXAMPLE
SCALE:6X

SOLDER MASK
OPENING

METAL

METAL UNDER
SOLDER MASK

SOLDER MASK
OPENING

0.07 MAX
ALL AROUND

0.07 MIN
ALL AROUND

NON SOLDER MASK
DEFINED

SOLDER MASK
DEFINED

SOLDER MASK DETAILS

4220724/A   05/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

20X (2)

1

20X (0.6)

18X (1.27)

SYMM

SYMM

20

10

11

(9.3)

SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:6X

4220724/A   05/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

C — SEATING PLANE

0.1 C

6.6 / 6.2 TYP

A

PIN 1 INDEX AREA

1

20

18X 0.65

2X 5.85

6.6 / 6.4 NOTE 3

10

11

20X 0.30 / 0.19

B

4.5 / 4.3 NOTE 4

⊕ 0.1 Ⓜ C A B

1.2 MAX

SEE DETAIL A

(0.15) TYP

0.25 GAGE PLANE

0° -8°

0.75 / 0.50

0.15 / 0.05

DETAIL A
TYPICAL

4220206/A   02/2017

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

20X (1.5)

SYMM

(R0.05) TYP

1

20X (0.45)

20

18X (0.65)

SYMM

10

11

(5.8)

LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

SOLDER MASK
OPENING

METAL

EXPOSED METAL

0.05 MAX
ALL AROUND

NON-SOLDER MASK
DEFINED
(PREFERRED)

METAL UNDER
SOLDER MASK

SOLDER MASK
OPENING

EXPOSED METAL

0.05 MIN
ALL AROUND

SOLDER MASK
DEFINED

SOLDER MASK DETAILS

4220206/A   02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

20X (1.5)

SYMM

(R0.05) TYP

20X (0.45)

1

20

18X (0.65)

SYMM

10

11

(5.8)

4220206/A   02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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